

The 21st Korean Conference on Semiconductors
제21회 한국반도체학술대회
February 24–26, 2014 / Hanyang University, Seoul, Korea

F. Silicon Device and Integration Technology 분과

[WG1-F] Emerging Device Technologies

Date	Feb. 26, 2014 (Wed.)
Place	Room G / 제1공학관 405호 (# 405, Engineering Building I)

Session Chair: 노태문 박사(ETRI), 최우영 교수(서강대학교)

- WG1-F-1 10:50-11:20 SiGeSn Ternary System for Next-Generation Electronic and Photonic Devices**
저자: Seongjae Cho¹, Byung-Gook Park², and James S. Harris Jr.³
소속: ¹Department of Electronic Engineering, Gachon University, ²Inter-university Semiconductor Research Center (ISRC) with Department of Electrical and Computer Engineering, Seoul National University, ³Department of Electrical Engineering, Stanford University
- WG1-F-2 11:20-11:35 Optimization of Integration Process for Stabilized Graphene MOSFET**
저자: 김윤지, 이영곤, 강창구, 정욱진, 이상철, 이상경, 이병훈
소속: School of Materials Science and Engineering, Gwangju Institute of Science and Technology
- WG1-F-3 11:35-11:50 Integrate-and-Fire Neuron Circuit and Synaptic Device with Floating Body MOSFETs**
저자: Min-Woo Kwon, Hyungjin Kim, Jungjin Park, and Byung-Gook Park
소속: ISRC and Department of Electrical and Computer Engineering, Seoul National University
- WG1-F-4 11:50-12:05 Schottky Barrier Tunneling Field-Effect Transistor using Spacer Technique**
저자: Hyun Woo Kim, Jong Pil Kim, Sang Wan Kim, Min-Chul Sun, Garam Kim, Jang Hyun Kim, Euyhwan Park, and Byung-Gook Park
소속: Department of Electrical Engineering and Computer Science, Seoul National University